JUN 1 8 2002

UNITED STATES PATENT AND TRADEMARK OFFICE

ATTY.'S DOCKET: KAGADEI=1

In re Application of:

Art Unit: 2838

V. KAGADEI et al.

Examiner:

Appln. No.: 10/086,621

Washington, D.C.

Filed: March 4, 2002

June 18, 2002

For: METHOD AND APPARATUS

FOR PRODUCING ATOMIC ...

INFORMATION DISCLOSURE STATEMENT [IDS]

Honorable Commissioner of Patents and Trademarks Washington, D.C. 20231

Sir:

This Information Disclosure Statement is submitted in accordance with 37 CFR §\$1.97, 1.98, and it is requested that the information set forth in this statement and in the listed documents be considered during the pendency of the aboveidentified application, and any other application relying on the filing date of the above-identified application or crossreferencing it as a related application.

- [X] 1. This IDS should be considered, in accordance with 37 CFR \$1.97, as it is filed before the mailing date of a first office action on the merits.
- [X] 2. In accordance with 37 CFR \$1.98, list (e.g., includes form PTO-1449) of all publications, or other information submitted for consideration by the office, either incorporated into this IDS or as an attachment hereto. A copy of each document listed is attached.

- [X] 3. Documents \underline{AD} , \underline{AQ} , \underline{AX} and \underline{AZ} is not in the English language. In accordance with \$1.98(c), Applicant(s) states:
 - [X] An English translation of each document AD, AQ, AX and AZ (or of the pertinent portions thereof), or a copy of each corresponding English-language patent or application, or English-language abstract (or claim) is enclosed.
- [X] 4. No explanation of relevance is necessary for documents in the English language (see reply to Comments 67 and 68 in the preamble to the final rules; 1135 OG 13 at 20).
- [] 5. Other information being provided for the examiner's consideration follows:
- 6. In accordance with 37 CFR §\$1.97(g) and (h), the filing of this IDS should not be construed representation that a search has been made or that information cited is, or is considered to be, material to patentability as defined in §1.56 (b), or that any cited document listed or attached is (or constitutes) prior art. Unless otherwise indicated, the date of publication indicated for an item is taken from the face of the item and Applicant(s) reserves the right to prove that the date of publication is in fact different.

Respectfully submitted,

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Substitute for form 1449A/I INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known					
Application Number 10/086,621					
Filing Date	March 4, 2002				
First Named Invent r	V. KAGADEI et al.				
Group Art Unit					
Examiner Name					
Attorney Docket Number	KAGADEI=1				

·				U.S. PATENT DOCUM	MENTS	
Examiner nitials*	Cite No.1	U.S. Patent Number	Document Kind Code ² (if known)	Name of Patentee or Applicant/Inventor	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	5,336,533		BALMASHNOV et al.	Aug. 9, 1994	
	AB	5,693,173		COLOMBO et al.	Dec. 2, 1997	
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			Foreign Patent Nu		Name of Patentee or	Date of Publication		
Examiner Initials*	Cite No.1	Office ³	Number	Kind Code ⁵ (if known)	Applicant/Inventor of Cited Document	of Cited Document MM-DD-YYYY	Where Relevant Passages or Relevant Figures Appear	T⁵
	AX	RU	2088056		KAGADEJ et al.	Aug. 2, 1997		xxx
			 					
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

JUN 1 8 2002		•	PTO/SB/57 (10/96)
Substitute for form 14/99/PTO	С	omplete if Known	
TRANS	Application Number	10/086,621	
INFORMATION DISCLOSURE	Filing Date	March 4, 2002	
STATEMENT BY APPLICANT	First Named Inventor	V. KAGADEI et al.	
	Group Art Unit		
(use as many sheets as necessary)	Examiner Name		

Attorney Docket Number

KAGADEI=1

Sheet

of

	OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Cite No.1	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
AC	LEONE, "Kinetic-Energy-Enhanced Neutral Etching", <u>Jpn. J. Appl. Phys.</u> , (1995), vol. 34, No. 4B, pages 20-73-2082	
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AE	ROUSSEAU et al., "Pulsed microwave discharge: a very efficient H atom source", <u>J. Phys. D: Phys.</u> , (1994), vol 27, pages 2439-2441	
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AM	EPI MBE Production Group. Aug./Sept., 1994, Applications Note, "On the Use of Atomic Hydrogen in MBE"	
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Examiner	 Date	
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¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

JUN 18 2002		PTO/SB/57 (10/96)
Substitute for form 1449 PZO	Co	omplete if Known
Substitute form 1449 PTO	Application Number	10/086,621
INFORMATION DISCLOSURE	Filing Date	March 4, 2002
STATEMENT BY APPLICANT	First Named Inventor	V. KAGADEI et al.
	Group Art Unit	
(use as many sheets as necessary)	Examiner Name	
Sheet 3 of 3	Attorney Docket Number	KAGADEI=1

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²
	AO	LIVSHITS et al., "Dissociation of hydrogen molecules on Metal filaments in H ion sources", <u>Plasma Cource Sci. Technol.</u> , (1994), pages 465-472	
	AP	HOFLUND et al., "Performance Characteristics of a hyperthermal oxygen-atom generator", Meas. Sci. Technol., (1994), vol 5, pages 201-204	
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	ВА	ITO et al., "Purification of diamond films by applying current into the plasma stream in the arc discharge plasma jet chemical vapor deposition technique", <u>J. Appl. Phys.</u> , (1995), vol. 77, No. 12, Pages 6636-6640	

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